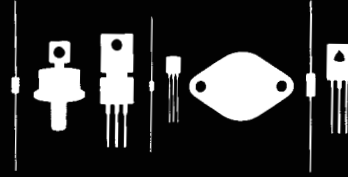


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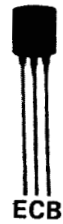
145 Adams Avenue
Hauppauge, New York 11788



2N4058
2N4059
2N4060
2N4061
2N4062

SILICON PNP TRANSISTOR

JEDEC TO-92 CASE



DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N4058 series types are Molded Epoxy Silicon PNP Transistors designed for low level, low noise (2N4058) and Low level, high gain (2N4059, 2N4060, 2N4061, 2N4062) applications. Recommended NPN complementary series is 2N3707 thru 2N3711.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNIT
Collector-Base Voltage	V _{CB0}	30	V
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter-Base Voltage	V _{EB0}	6.0	V
Collector Current	I _C	200	mA
Power Dissipation	P _D	625	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 TO +150°C	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C)

SYMBOL	TEST CONDITIONS	2N4058		2N4059		2N4060		2N4061		2N4062		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
I _{CBO}	V _{CB} =20V		100		100		100		100		100	ηA
I _{EBO}	V _{EB} =6.0V		100		100		100		100		100	ηA
BV _{CEO}	I _C =1.0mA	30		30		30		30		30		V
V _{CE(SAT)}	I _C =10mA, I _B =0.5mA		0.7		0.7		0.7		0.7		0.7	V
V _{BE(ON)}	V _{CE} =5.0V, I _C =1.0mA	0.5	1.0	0.5	1.0	0.5	1.0	0.5	1.0	0.5	1.0	V
h _{FE}	V _{CE} =5.0V, I _C =100μA	100	400									
h _{FE}	V _{CE} =5.0V, I _C =1.0mA			45	660	45	165	90	330	180	660	
h _{fe}	V _{CE} =5.0V, I _C =100μA, f=1kHz	100	550									
h _{fe}	V _{CE} =5.0V, I _C =1.0mA f=1kHz			45	800	45	250	90	450	180	800	
NF	V _{CE} =5.0V, I _C =100μA, R _G =5KΩ, BW=15.7kHz (2N4058 only)		5.0		-		-		-		-	dB

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